HFZT

PXT2907A

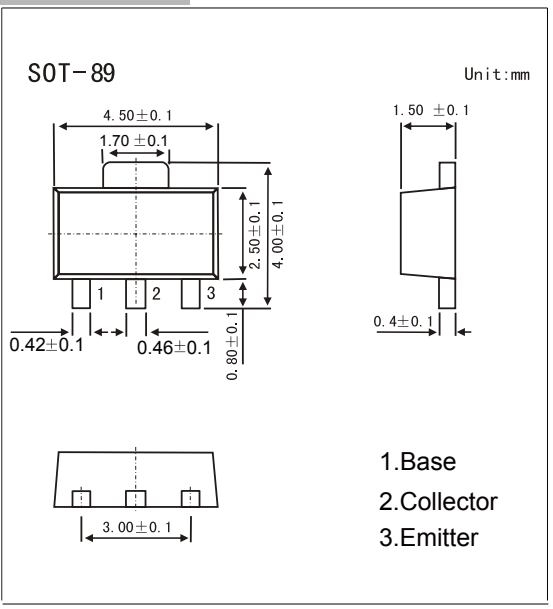
SOT-89 Plastic-Encapsulate Transistors

Features

- Switching and Linear Amplification
- High Current and Low Voltage
- Complement to PXT2222A
- PNP Transistors

MECHANICAL DATA

- Case style:SOT-89molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-60	V
Collector - Emitter Voltage	V_{CEO}	-60	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-600	mA
Collector Power Dissipation	P_C	500	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	250	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -1 mA， I_E= 0	-60			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -10 mA， I_B= 0	-60			
Emitter - base breakdown voltage	V_{EBO}	I_E= -1 mA， I_C= 0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -50 V , I_E= 0			-50	nA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-50	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500 mA, I_B=-50mA			-1.6	V
		I_C=-500 mA, I_B=-15mA			-0.4	
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-500 mA, I_B=-50mA			-2.6	
		I_C=-500 mA, I_B=-15mA			-1.3	
DC current gain	$h_{FE(1)}$	V_{CE}= -10V, I_C= -0.1mA	75			
	$h_{FE(2)}$	V_{CE}= -10V, I_C= -1mA	100			
	$h_{FE(3)}$	V_{CE}= -10V, I_C= -10mA	100			
	$h_{FE(4)}$	V_{CE}= -10V, I_C= -150mA	100		300	
	$h_{FE(5)}$	V_{CE}= -10V, I_C= -500mA	50			
Delay time	t_d	V_{CC}=-30V, I_C=-150mA I_{B1}=- I_{B2}= -15mA			12	ns
Rise time	t_r				30	
Storage time	t_s				300	
Fall time	t_f				65	
Transition frequency	f_T	V_{CE}= -10V, I_C= -20mA,f=100MHz	200			MHz

■ Marking

Marking	*2F